

Data sheet acquired from Harris Semiconductor SCHS056D – Revised August 2003

CMOS OR Gates

High-Voltage Types (20-Volt Rating)

Quad 2-Input OR Gate CD4072B Dual 4-Input OR CD4075B Triple 3-Input OR

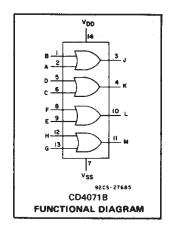
■ CD4071B, CD4072B, and CD4075B OR gates provide the system designer with direct implementation of the positive-logic OR function and supplement the existing family of CMOS gates.

The CD4071B, CD4072B, and CD4075B types are supplied in 14-lead hermetic dual-in-line ceramic packages (F3A suffix), 14-lead dual-in-line plastic packages (E suffix), 14-lead small-outline packages (M, MT, M96, and NSR suffixes), and 14-lead thin shrink small-outline packages (PW and PWR suffixes).

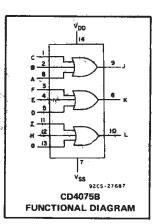
CD4071B, CD4072B, CD4075B Types

Features:

- Medium-Speed Operation-tp $_{LH}$, t_{PHL} = 60 ns (typ.) at V_{DD} = 10 V
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Standardized, symmetrical output characteristics
- Noise margin (over full package temperature range)
 - 1 V at V_{DD} = 5 V 2 V at VDD = 10 V
 - 2.5 V at VDD = 15 V
- 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"



9205-27686 CD4072B **FUNCTIONAL DIAGRAM**



RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	UNITS	
	MIN.	MAX.	
Supply-Voltage Range (For TA = Full Package-Temperature Range)	3	18	٧

STATIC ELECTRICAL CHARACTERISTICS

CHARACTER-	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							
ISTIC	Vo	VIN (V)	VDD					+25			UNITS
	(V)		(V)	-55	40	+85	+125	Min.	Тур.	Max.]
Quiescent Device	_	0,5	5	0.25	0.25	7.5	7.5	_	0.01	0.25	μΑ
Current,		0,10	10	0.5	0,5	15	15	-	0.01	0,5	
IDD Max.	-	0,15	15	1	1	30	30	-	0.01	1	
	-	0,20	20	5	5	150	150	-	0.02	5	
Output Low	0.4	0,5	5	0.64	0.61	0.42	0,36	0.51	1	-	
(Sink) Current	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	-	
IOL Min.	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	_	mA
Output High	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	_	
(Source)	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	-	
Current, IOH Min.	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	_	
TOH WIIII.	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	-	
Output Voltage:	_	0,5	5	0.05			-	0	0.05	V	
Low-Level, VOI Max.	_	0,10	10	0.05				-	0		0.05
VUL 1898X.	_	0,15	15	0.05				_	0		0.05
Output Voltage:	_	0,5	5	4.95			4.95	5	-		
High-Level, VOH Min.	_	0,10	10	9.95				9.95	10		-
AOH MIII.	_	0,15	15	14.95				14.95	15		-
Input Low	0.5, 4.5		. 5	1.5				_	Γ –	1.5	
Voltage,	1, 9	_	10	3				-	_	3	
VIL Max.	1.5,13.5	+	15	4				_	_	4	
Input High Voltage, VIH Min.	4.5	1	5	3.5			3.5			· •	
	9	, , ,	10	7				7			
	13.5		15	11			11	<u> </u>	_		
Input Current IJN Max.	i i	0,18	18	±0.1	±0.1	±1	±1	<u>-</u> :	±10 ⁻⁵	±0.1	μА

CD4071B, CD4072B, CD4075B Types

MAXIMUM RATINGS, Absolute-Maximum Values:	
DC SUPPLY-VOLTAGE RANGE, (VDD)	'
Voltages referenced to VSS Terminal)0.5\	/ to +20V
INPUT VOLTAGE RANGE, ALL INPUTS0.5V to V	+0.5V
DC INPUT CURRENT, ANY ONE INPUT	
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -55°C to +100°C	500mW
For T _A = +100°C to +125°C	200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR TA = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)	100mW
OPERATING-TEMPERATURE RANGE (TA)55°C to	+125°C
STORAGE TEMPERATURE RANGE (Tstg)65°C to	+150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 inch (1.59 \pm 0.79mm) from case for 10s max	+265°C

DYNAMIC ELECTRICAL CHARACTERISTICS at T_A = 25°C, Input t_r, t_f = 20 ns, and C_L = 50 pF, R_L = 200 $\,k\Omega$

CHARACTERISTIC	TEST COND	ITIONS	ALL 1	UNITS	
		V _{DD} VOLTS	TYP.	MAX.	OWITS
Propagation Delay Time, tpHL, tpLH		5 10 15	125 60 45	250 120 90	ns
Transition Time, ^t THL ^{, t} TLH		5 10 15	100 50 40	200 100 80	ns
Input Capacitance, CIN	Any Input	1-1	5	7.5	pF

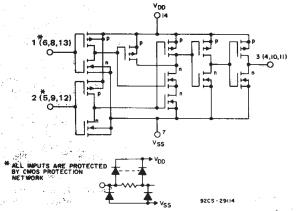


Fig. 3 - Schematic diagram for CD40718 (1 of 4 identical gates).

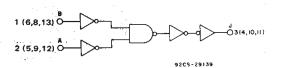


Fig. 5 -/ Logic diagram for CD4071B (1 of 4 identical gates).

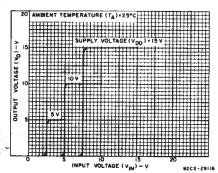


Fig. 1 — Typical voltage transfer characteristics.

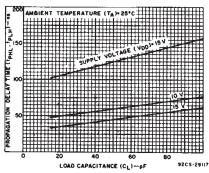


Fig. 2 — Typical propagation delay time as a function of load capacitance.

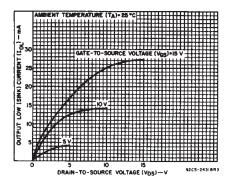


Fig. 4 — Typical output low (sink) current characteristics.

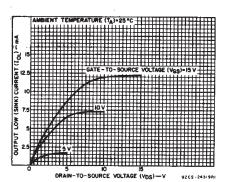


Fig. 6 — Minimum output low (sink) current characteristics.